

DEVICE AND METHOD FOR MULTICRYSTALLINE SILICON WAFERS

Abstract

A method for making ingots, and devices for making ingots are provided.

- 5 Crucibles are provided that are reusable for forming multicrystalline silicon ingots. Crucibles are provided with features such as multiple components, coefficients of thermal expansion, and coatings that enhance a release of the ingots from the crucibles after cooling. Coatings on crucibles are provided that reduce or eliminate contamination of silicon ingots during formation. Methods of forming composite
- 10 wafers are provided that produce a low cost wafer without sacrificing performance.

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